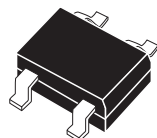


CBR1F-D020S SERIES

**1.0 AMP DUAL IN LINE
FAST RECOVERY
SILICON BRIDGE RECTIFIER**



SMDIP CASE

CentralTM
Semiconductor Corp.

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CBR1F-D020S Series types are fast recovery, full wave bridge rectifiers mounted in a durable epoxy surface mount molded case, utilizing glass passivated chips. To order devices on tape and reel (1,000/13" reel) add TR13 suffix.

MARKING CODE: FULL PART NUMBER

MAXIMUM RATINGS: (T_A=25°C unless otherwise specified)

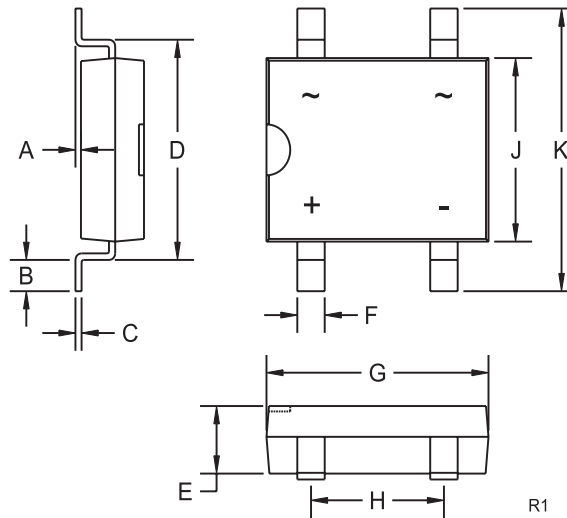
	<u>SYMBOL</u>	<u>CBR1F- D020S</u>	<u>CBR1F- D040S</u>	<u>CBR1F- D060S</u>	<u>CBR1F- D080S</u>	<u>CBR1F- D100S</u>	<u>UNITS</u>
Peak Repetitive Reverse Voltage	V _{RRM}	200	400	600	800	1000	V
DC Blocking Voltage	V _R	200	400	600	800	1000	V
RMS Reverse Voltage	V _{R(RMS)}	140	280	420	560	700	V
Average Forward Current (T _A =40°C)	I _O			1.0			A
Peak Forward Surge Current	I _{FSM}			50			A
Rating for Fusing (t<8.35ms)	I ² t			3.74			A ² s
Operating and Storage Junction Temperature	T _J , T _{stg}			-65 to +150			°C

ELECTRICAL CHARACTERISTICS PER DIODE (T_A=25°C unless otherwise noted)

<u>SYMBOL</u>	<u>TEST CONDITIONS</u>	<u>MIN</u>	<u>TYP</u>	<u>MAX</u>	<u>UNITS</u>
I _R	V _R =Rated V _{RRM}			5.0	μA
I _R	V _R =Rated V _{RRM} ; T _A =125°C			0.5	mA
V _F	I _F =1.0A			1.3	V
t _{rr} (200V thru 400V)	I _F =0.5A, I _R =1.0A, Recov. to 0.25A			200	ns
t _{rr} (600V)	I _F =0.5A, I _R =1.0A, Recov. to 0.25A			300	ns
t _{rr} (800V, 1000V)	I _F =0.5A, I _R =1.0A, Recov. to 0.25A			500	ns
C _J	V _R =4.0V, f=1.0MHz		25		pF

R0 (14-January 2003)

SMDIP CASE - MECHANICAL OUTLINE



DIMENSIONS				
SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.004	0.008	0.10	0.20
B	0.040	0.060	1.02	1.52
C	0.009		0.23	
D	0.290	0.310	7.37	7.87
E	0.086	0.098	2.18	2.49
F	0.038	0.042	0.97	1.07
G	0.316	0.335	8.03	8.51
H	0.195	0.205	4.95	5.21
J	0.245	0.255	6.22	6.48
K	0.360	0.410	9.14	10.41

SMDIP (REV: R1)

MARKING CODE: FULL PART NUMBER

R0 (14-January 2003)